

**IN THE SPECIFICATION:**

Please amend the paragraph at page 3, lns. 7-10 as follows:

A high melting point metal film (tungsten) obtained as such includes scarce impurity elements, typically, amount of oxygen included could be reduced to no more than 30 parts per million (ppm), and an electric resistivity of  $20 \mu\Omega\cdot\text{cm}$  or less, typically  $6-15 \mu\Omega\cdot\text{cm}$  could be obtained. The stress of the film was  $-5\times10^9-5\times10^9 \text{dyn/cm}^2$ .

Please amend the paragraph at page 30, lns. 9-12 as follows:

The structure of the storage capacitor of the present invention is not necessarily limited to the one shown in embodiment 1. For example, the storage capacitor described in Japanese Patent Application Laid-Open No. Hei 9-316567 (Publication No. Hei 11-133463) or Japanese Patent Application Laid-Open No. Hei 10-254097 (Publication No. 2001-56485) may be used.